

SN74LVC2G66 双路双边模拟开关

1 特性

- 采用德州仪器 (TI) 的 NanoFree™ 封装
- 1.65V 至 5.5V V_{CC} 运行
- 输入接受的电压达到 5.5V
- 电压为 3.3V 时, t_{pd} 最大值为 0.8ns
- 高开关输出电压比
- 高度线性
- 高速, 典型值 0.5ns (V_{CC}=3V, C_L=50pF)
- 轨至轨输入/输出
- 低导通电阻, 典型值为 $\approx 6\ \Omega$ (V_{CC} = 4.5V)
- 锁断性能超过 100mA, 符合 JESD 78 II 类规范的要求

2 应用

- 无线设备
- 音频和视频信号路由
- 便携式计算
- 可穿戴设备
- 信号门控、斩波、调制或解调 (调制解调器)
- 适用于模数和数模转换系统的信号多路复用

3 说明

该双路双向模拟开关适用于 1.65V 至 5.5V V_{CC} 运行环境。

SN74LVC2G66 器件可处理模拟信号和数字信号。SN74LVC2G66 器件允许在任意方向传输振幅高达 5.5V (峰值) 的信号。

NanoFree 封装技术是 IC 封装概念上的一项重大突破, 它将裸片用作封装。

每个开关部分有其自己的输入使能控制 (C)。应用到 C 上的一个高电平电压开启相关开关部分。

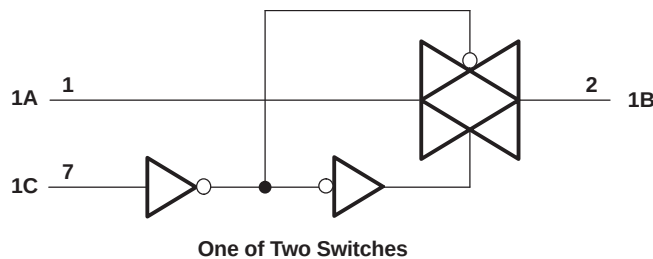
应用 包括信号门控、斩波、调制或解调 (调制解调器) 以及适用于模数和数模转换系统的信号多路复用。

器件信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
SN74LVC2G66DCT	SSOP (8)	2.95mm × 2.80mm
SN74LVC2G66DCU	超薄小外形尺寸封装 (VSSOP)(8)	2.30mm × 2.00mm
SN74LVC2G66YZP	DSBGA (8)	1.91mm × 0.91mm

(1) 如需了解所有可用封装, 请参阅数据表末尾的可订购产品附录。

逻辑图、每次转换 (正逻辑)



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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision M (May 2018) to Revision N Page

•	Changed the YZP pin configuration	3
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Changes from Revision L (September 2015) to Revision M Page

•	Updated pinout image and the <i>Pin Function</i> table	3
•	Changed pin 3 Name From: 1C To: 2C	3
•	Changed the <i>Thermal Information</i> table for the DCT package	5

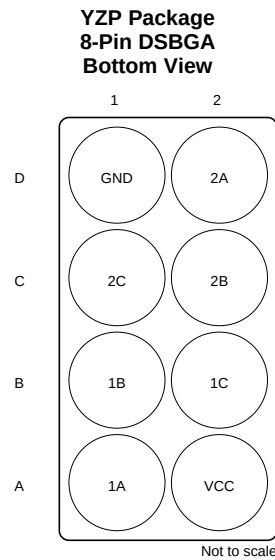
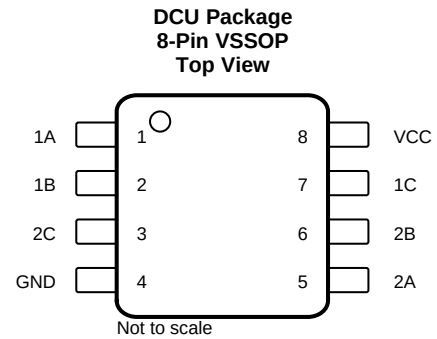
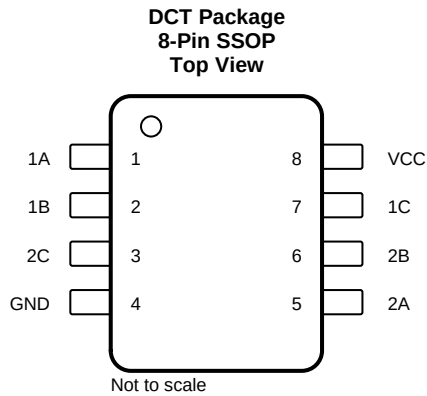
Changes from Revision K (January 2014) to Revision L Page

•	添加了应用 部分、器件信息 表、引脚配置和功能 部分、ESD 额定值 表、典型值 部分、特性 说明 部分、器件功能模 式、应用和实施 部分、电源建议 部分、布局 部分、器件和文档支持 部分以及机械、封装和可订购信息 部分	1
•	Added <i>Thermal Information</i> table	5

Changes from Revision J (December 2011) to Revision K Page

•	将文档更新为新的 TI 数据表格式 - 规格没有变化。	1
•	删除了订购信息 表。	1

5 Pin Configuration and Functions



See mechanical drawings for dimensions.

Pin Functions

NAME	PIN		I/O	DESCRIPTION
	DCT DCU	YZP		
1A	1	A1	I/O	Bidirectional signal to be switched
1B	2	B1	I/O	Bidirectional signal to be switched
2C	3	C1	I	Controls the switch (L = OFF, H = ON)
2A	5	D2	I/O	Bidirectional signal to be switched
2B	6	C2	I/O	Bidirectional signal to be switched
1C	7	B2	I	Controls the switch (L = OFF, H = ON)
GND	4	D1	—	Ground pin
V _{CC}	8	A2	—	Power pin

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage ⁽²⁾	−0.5	6.5	V
V _I	Input voltage ⁽²⁾⁽³⁾	−0.5	6.5	V
V _O	Switch I/O voltage ⁽²⁾⁽³⁾⁽⁴⁾	−0.5	V _{CC} + 0.5	V
I _{IK}	Control input clamp current	V _I < 0	−50	mA
I _{I/O}	I/O port diode current	V _{I/O} < 0 or V _{I/O} > V _{CC}	−50	mA
I _T	On-state switch current	V _{I/O} = 0 to V _{CC}	±50	mA
	Continuous current through V _{CC} or GND		±100	mA
T _{stg}	Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to ground, unless otherwise specified.
- (3) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (4) This value is limited to 5.5 V maximum.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

See ⁽¹⁾.

		MIN	MAX	UNIT
V _{CC}	Supply voltage	1.65	5.5	V
V _{I/O}	I/O port voltage	0	V _{CC}	V
V _{IH}	High-level input voltage, control input	V _{CC} = 1.65 V to 1.95 V	V _{CC} × 0.65	V
		V _{CC} = 2.3 V to 2.7 V	V _{CC} × 0.7	
		V _{CC} = 3 V to 3.6 V	V _{CC} × 0.7	
		V _{CC} = 4.5 V to 5.5 V	V _{CC} × 0.7	
V _{IL}	Low-level input voltage, control input	V _{CC} = 1.65 V to 1.95 V	V _{CC} × 0.35	V
		V _{CC} = 2.3 V to 2.7 V	V _{CC} × 0.3	
		V _{CC} = 3 V to 3.6 V	V _{CC} × 0.3	
		V _{CC} = 4.5 V to 5.5 V	V _{CC} × 0.3	
V _I	Control input voltage	0	5.5	V
Δt/Δv	Input transition rise or fall time	V _{CC} = 1.65 V to 1.95 V	20	ns/V
		V _{CC} = 2.3 V to 2.7 V	20	
		V _{CC} = 3 V to 3.6 V	10	
		V _{CC} = 4.5 V to 5.5 V	10	
T _A	Operating free-air temperature	−40	85	°C

- (1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LVC2G66			UNIT
		DCT (SSOP)	DCU (VSSOP)	YZP (DSBGA)	
		8 PINS	8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	186.1	204.4	102	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	116.5	77	—	°C/W
R _{θJB}	Junction-to-board thermal resistance	98.6	83.2	—	°C/W
ψ _{JT}	Junction-to-top characterization parameter	42.2	7.1	—	°C/W
ψ _{JB}	Junction-to-board characterization parameter	97.6	82.7	—	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	n/a	—	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V _{CC}	MIN	TYP ⁽¹⁾	MAX	UNIT
r _{on}	ON-state switch resistance	V _I = V _{CC} or GND, V _C = V _{IH} (see Figure 3 and Figure 1)	I _S = 4 mA	1.65 V		12.5	30	Ω
			I _S = 8 mA	2.3 V		9	20	
			I _S = 24 mA	3 V		7.5	15	
			I _S = 32 mA	4.5 V		6	10	
r _{on(p)}	Peak ON-state resistance	V _I = V _{CC} to GND, V _C = V _{IH} (see Figure 3 and Figure 1)	I _S = 4 mA	1.65 V		85	120 ⁽¹⁾	Ω
			I _S = 8 mA	2.3 V		22	30 ⁽¹⁾	
			I _S = 24 mA	3 V		12	20	
			I _S = 32 mA	4.5 V		7.5	15	
Δr _{on}	Difference of ON-state resistance between switches	V _I = V _{CC} to GND, V _C = V _{IH} (see Figure 3 and Figure 1)	I _S = 4 mA	1.65 V			7	Ω
			I _S = 8 mA	2.3 V			5	
			I _S = 24 mA	3 V			3	
			I _S = 32 mA	4.5 V			2	
I _{S(off)}	OFF-state switch leakage current	V _I = V _{CC} and V _O = GND or V _I = GND and V _O = V _{CC} , V _C = V _{IL} (see Figure 4)		5.5 V		±1		μA
						±0.1 ⁽¹⁾		
I _{S(on)}	ON-state switch leakage current	V _I = V _{CC} or GND, V _C = V _{IH} , V _O = Open (see Figure 5)		5.5 V		±1		μA
						±0.1 ⁽¹⁾		
I _I	Control input current	V _C = V _{CC} or GND		5.5 V		±1		μA
						±0.1 ⁽¹⁾		
I _{CC}	Supply current	V _C = V _{CC} or GND		5.5 V		10		μA
						1 ⁽¹⁾		
ΔI _{CC}	Supply-current change	V _C = V _{CC} – 0.6 V		5.5 V			500	μA
C _{ic}	Control input capacitance			5 V		3.5		pF
C _{io(off)}	Switch input / output capacitance			5 V		6		pF
C _{io(on)}	Switch input / output capacitance			5 V		14		pF

(1) T_A = 25°C

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6.6 Switching Characteristics

 over recommended operating free-air temperature range (unless otherwise noted) (see [Figure 2](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 1.8\text{ V} \pm 0.15\text{ V}$		$V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$		$V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$		$V_{CC} = 5\text{ V} \pm 0.5\text{ V}$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
$t_{pd}^{(1)}$	A or B	B or A		2		1.2		0.8		0.6	ns
$t_{en}^{(2)}$	C	A or B	2.3	10	1.6	5.6	1.5	4.4	1.3	3.9	ns
$t_{dis}^{(3)}$	C	A or B	2.5	10.5	1.2	6.9	2	7.2	1.1	6.3	ns

- (1) t_{PLH} and t_{PHL} are the same as t_{pd} . The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
- (2) t_{PZL} and t_{PZH} are the same as t_{en} .
- (3) t_{PLZ} and t_{PHZ} are the same as t_{dis} .

6.7 Analog Switch Characteristics

 $T_A = 25^\circ\text{C}$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V_{CC}	TYP	UNIT
Frequency response (switch on)	A or B	B or A	$C_L = 50\text{ pF}$, $R_L = 600\ \Omega$, $f_{in} = \text{sine wave}$ (see Figure 6)	1.65 V	35	MHz
				2.3 V	120	
				3 V	175	
				4.5 V	195	
			$C_L = 5\text{ pF}$, $R_L = 50\ \Omega$, $f_{in} = \text{sine wave}$ (see Figure 6)	1.65 V	>300	
				2.3 V	>300	
				3 V	>300	
				4.5 V	>300	
Crosstalk ⁽¹⁾ (between switches)	A or B	B or A	$C_L = 50\text{ pF}$, $R_L = 600\ \Omega$, $f_{in} = 1\text{ MHz}$ (sine wave) (see Figure 7)	1.65 V	–58	dB
				2.3 V	–58	
				3 V	–58	
				4.5 V	–58	
			$C_L = 5\text{ pF}$, $R_L = 50\ \Omega$, $f_{in} = 1\text{ MHz}$ (sine wave) (see Figure 7)	1.65 V	–42	
				2.3 V	–42	
				3 V	–42	
				4.5 V	–42	
Crosstalk (control input to signal output)	C	A or B	$C_L = 50\text{ pF}$, $R_L = 600\ \Omega$, $f_{in} = 1\text{ MHz}$ (square wave) (see Figure 8)	1.65 V	35	mV
				2.3 V	50	
				3 V	70	
				4.5 V	100	
Feedthrough attenuation (switch off)	A or B	B or A	$C_L = 50\text{ pF}$, $R_L = 600\ \Omega$, $f_{in} = 1\text{ MHz}$ (sine wave) (see Figure 9)	1.65 V	–58	dB
				2.3 V	–58	
				3 V	–58	
				4.5 V	–58	
			$C_L = 5\text{ pF}$, $R_L = 50\ \Omega$, $f_{in} = 1\text{ MHz}$ (sine wave) (see Figure 9)	1.65 V	–42	
				2.3 V	–42	
				3 V	–42	
				4.5 V	–42	

(1) Adjust f_{in} voltage to obtain 0 dBm at input.

Analog Switch Characteristics (continued)

$T_A = 25^\circ\text{C}$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V_{CC}	TYP	UNIT
Sine-wave distortion	A or B	B or A	$C_L = 50\text{ pF}$, $R_L = 10\text{ k}\Omega$, $f_{in} = 1\text{ kHz}$ (sine wave) (see Figure 10)	1.65 V	0.1%	
				2.3 V	0.025%	
				3 V	0.015%	
				4.5 V	0.01%	
			$C_L = 50\text{ pF}$, $R_L = 10\text{ k}\Omega$, $f_{in} = 10\text{ kHz}$ (sine wave) (see Figure 10)	1.65 V	0.15%	
				2.3 V	0.025%	
				3 V	0.015%	
				4.5 V	0.01%	

6.8 Operating Characteristics

$T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	$V_{CC} = 1.8\text{ V}$	$V_{CC} = 2.5\text{ V}$	$V_{CC} = 3.3\text{ V}$	$V_{CC} = 5\text{ V}$	UNIT
		TYP	TYP	TYP	TYP	
C_{pd} Power dissipation capacitance	$f = 10\text{ MHz}$	8	9	9.5	11	pF

6.9 Typical Characteristics

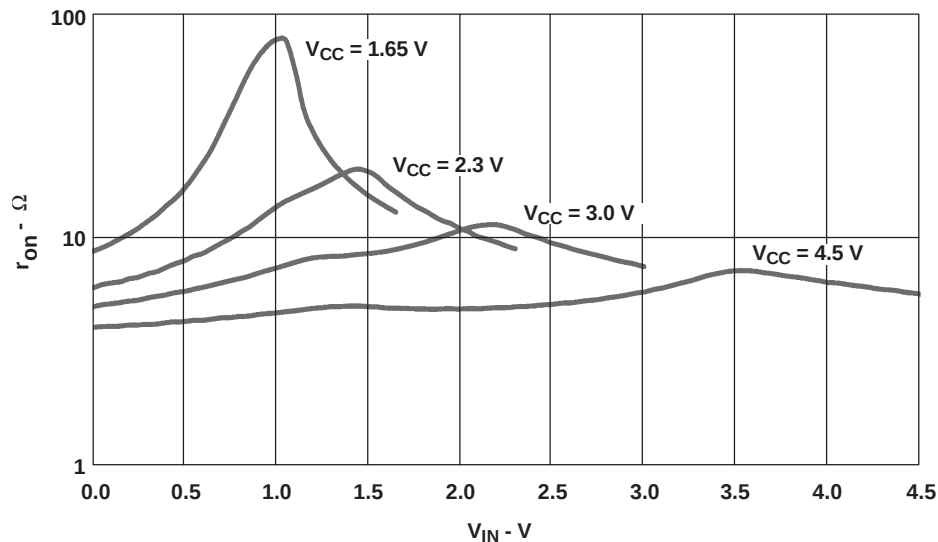
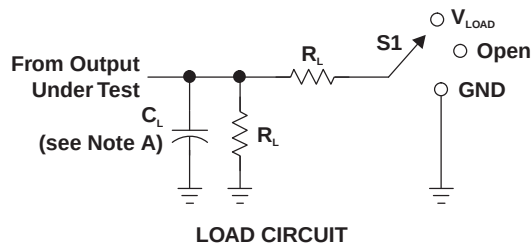


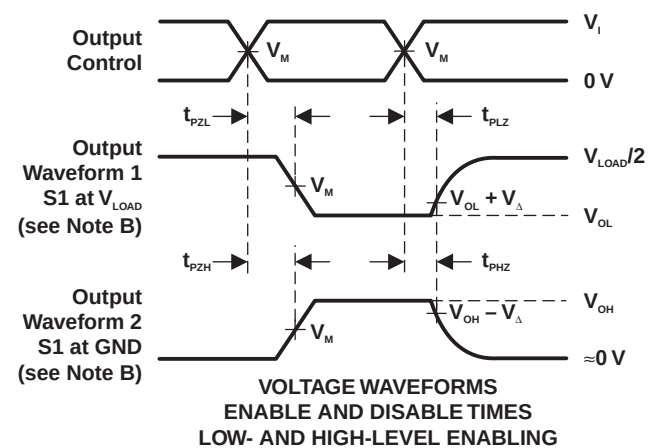
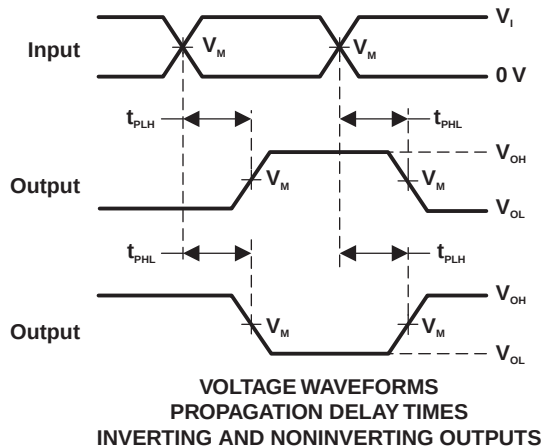
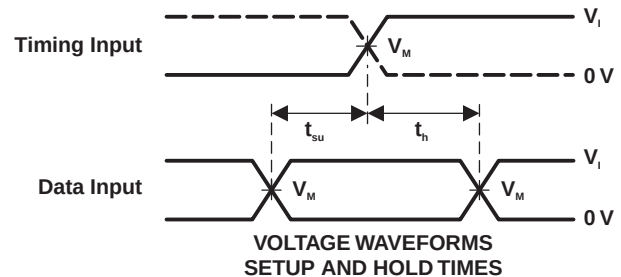
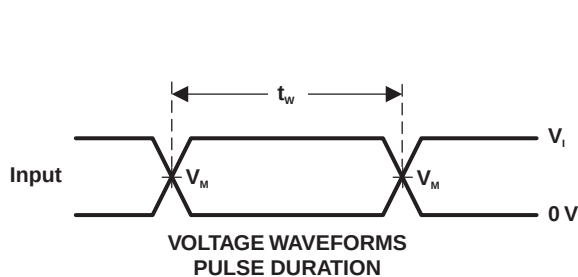
Figure 1. Typical r_{on} as a Function of Input Voltage (V_I) for $V_I = 0$ to V_{CC}

7 Parameter Measurement Information



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_i	t_f/t_r					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators have the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_o = 50\text{ }\Omega$.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .
 - All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

Parameter Measurement Information (continued)

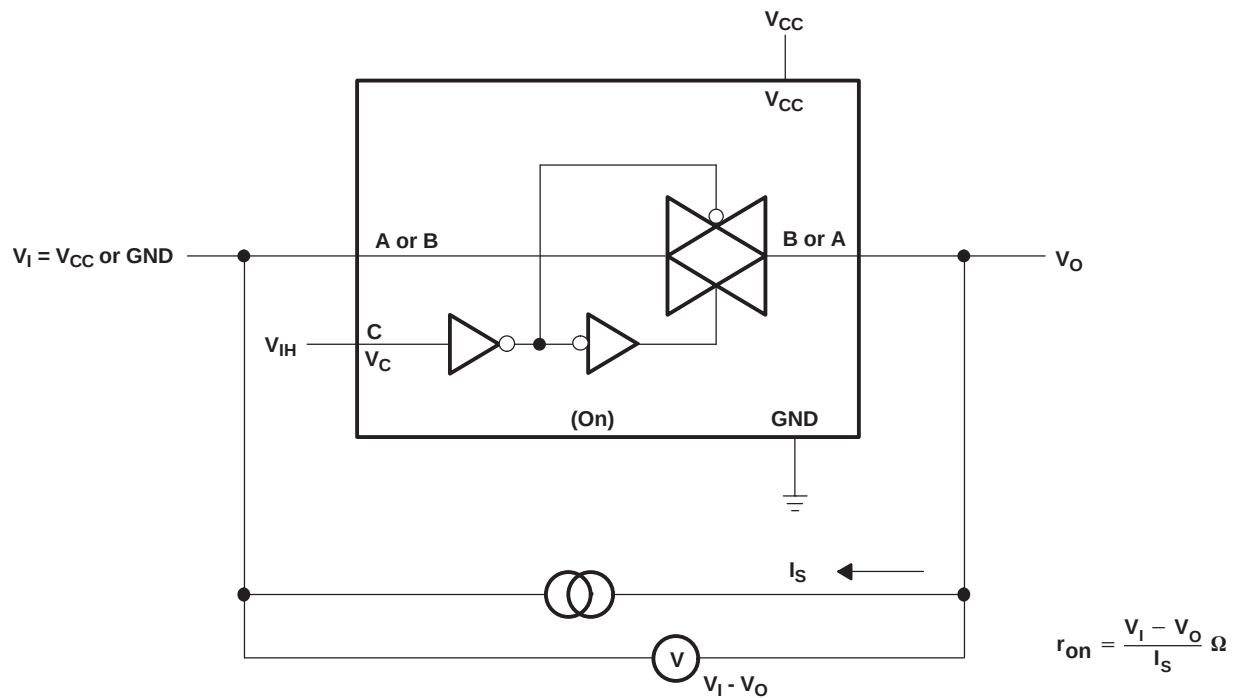


Figure 3. ON-State Resistance Test Circuit

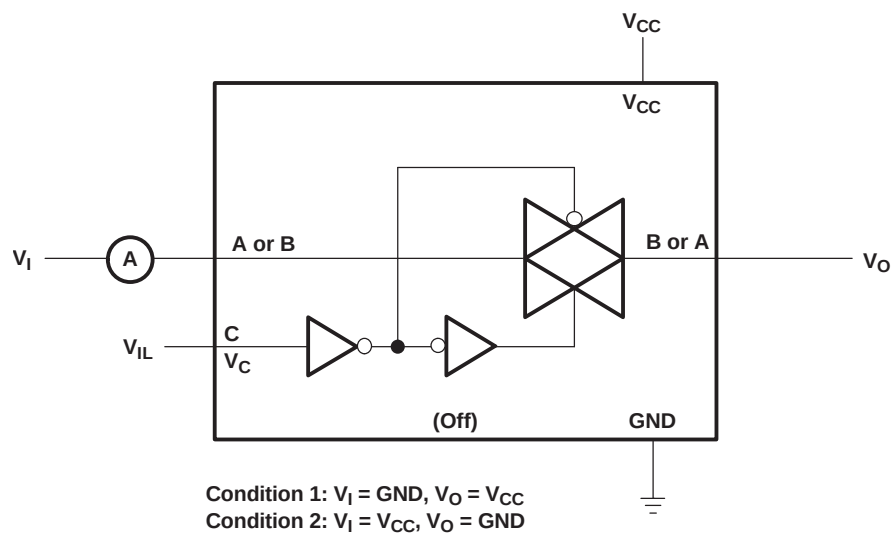


Figure 4. OFF-State Switch Leakage-Current Test Circuit

Parameter Measurement Information (continued)

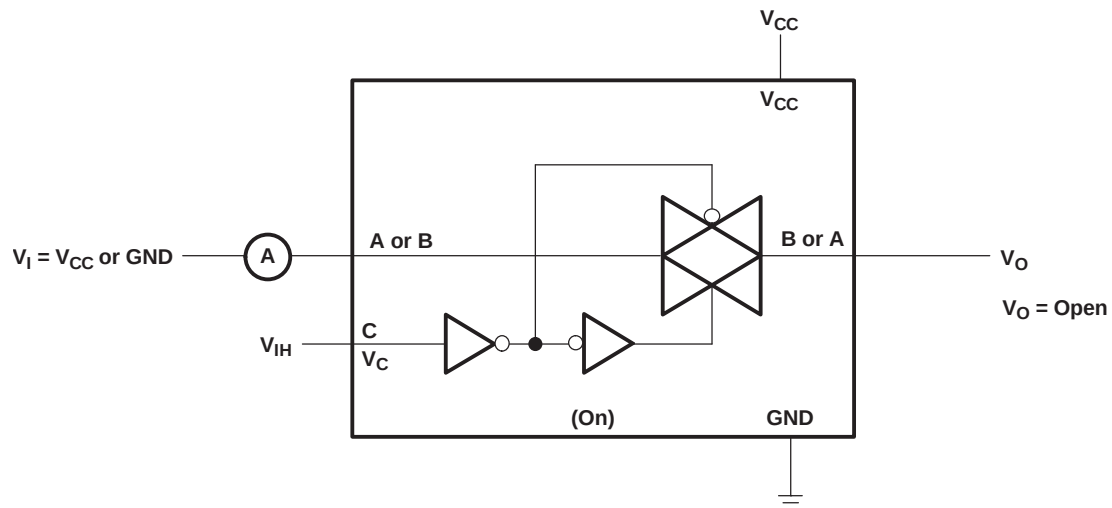


Figure 5. ON-State Leakage-Current Test Circuit

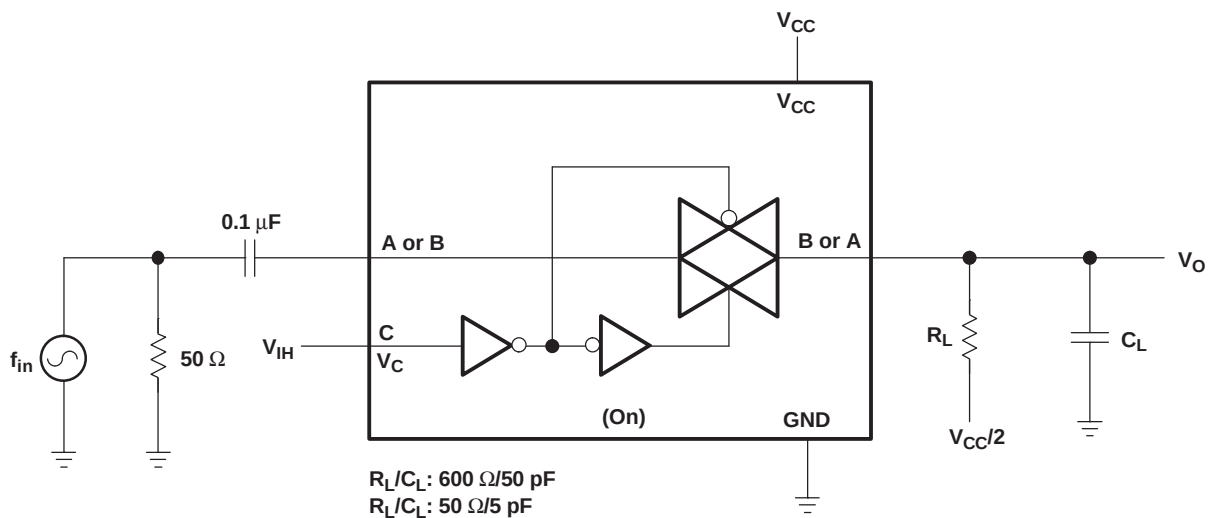


Figure 6. Frequency Response (Switch On)

The schematic diagram illustrates a 1-bit programmable gain amplifier (PGA) with two gain settings: (On) and (Off). The circuit is divided into two main sections, each containing a differential pair of transistors and a current mirror load.

(On) Section:

- The input signal f_{in} is coupled through a $50\ \Omega$ resistor and a $0.1\ \mu F$ capacitor to the input of the first differential pair (labeled 1A or 1B).
- The input signal V_{IH} is coupled through a $600\ \Omega$ resistor (R_{in}) to the input of the second differential pair (labeled 1B or 1A).
- The output of the first differential pair is connected to the input of the second differential pair through a current mirror load.
- The output of the second differential pair is connected to the output node V_{O1} through a $600\ \Omega$ resistor (R_L).
- The output node V_{O1} is connected to ground through a $50\ pF$ capacitor (C_L).
- The output voltage is V_{O1} .

(Off) Section:

- The input signal V_{IL} is coupled through a $600\ \Omega$ resistor (R_{in}) to the input of the first differential pair (labeled 2A or 2B).
- The input signal V_{IH} is coupled through a $600\ \Omega$ resistor (R_{in}) to the input of the second differential pair (labeled 2B or 2A).
- The output of the first differential pair is connected to the input of the second differential pair through a current mirror load.
- The output of the second differential pair is connected to the output node V_{O2} through a $600\ \Omega$ resistor (R_L).
- The output node V_{O2} is connected to ground through a $50\ pF$ capacitor (C_L).
- The output voltage is V_{O2} .

The circuit is powered by V_{CC} and GND . The output voltage is V_{O1} for the (On) section and V_{O2} for the (Off) section. The gain is determined by the ratio of the output voltage to the input voltage, expressed as $20\log_{10}(V_{O2}/V_{I1})$ or $20\log_{10}(V_{O1}/V_{I2})$.

The circuit diagram shows a 1-bit full adder implemented using a 74VHC00 hex inverters and a 74VHC14 Schmitt trigger. The inputs are $V_{CC}/2$ and V_C . The output is V_O . The circuit includes a 600 Ω resistor R_{in} and a 50 Ω resistor. The output is connected to a load resistor R_L (600 Ω) and a load capacitor C_L (50 pF). The power supply is V_{CC} and ground is GND.

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Parameter Measurement Information (continued)

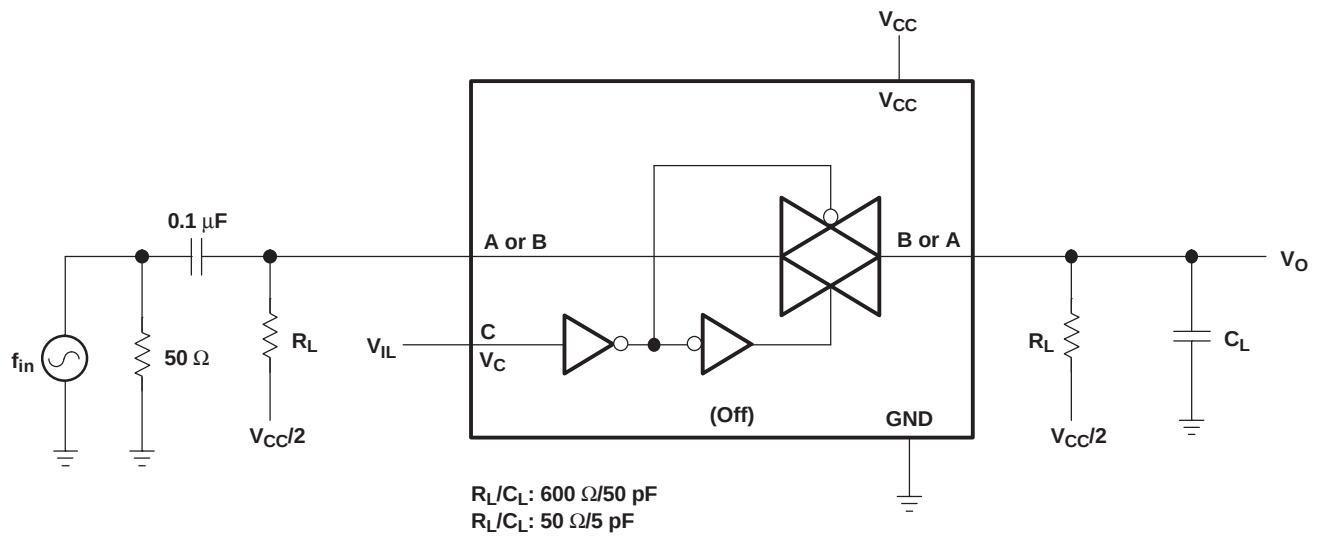


Figure 9. Feedthrough (Switch Off)

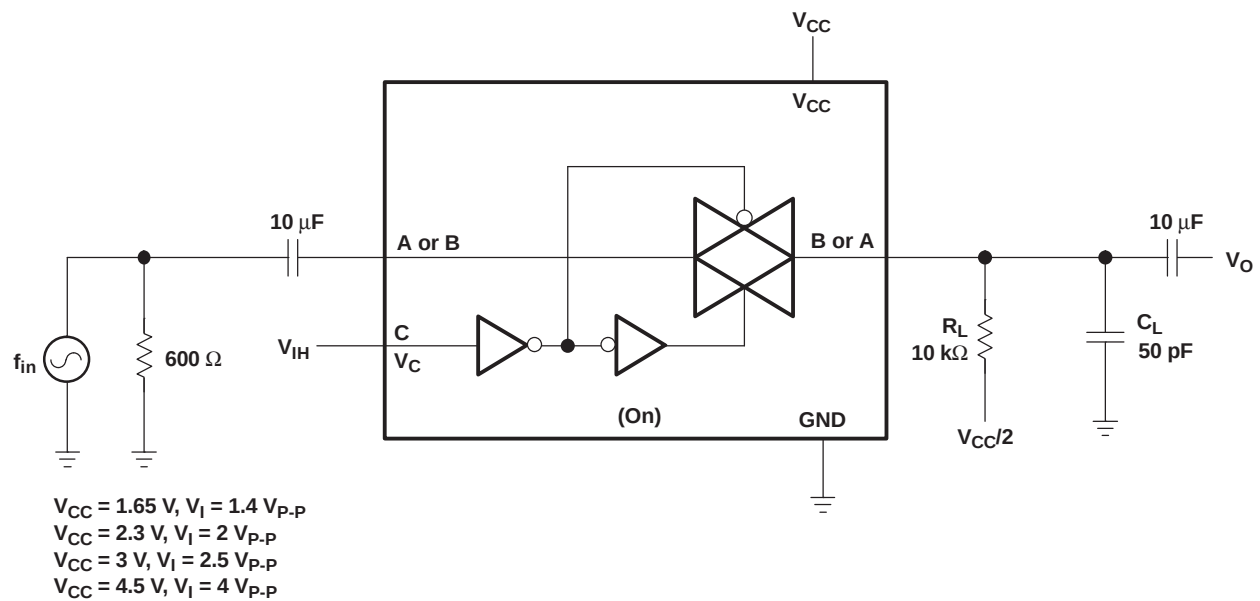


Figure 10. Sine-Wave Distortion

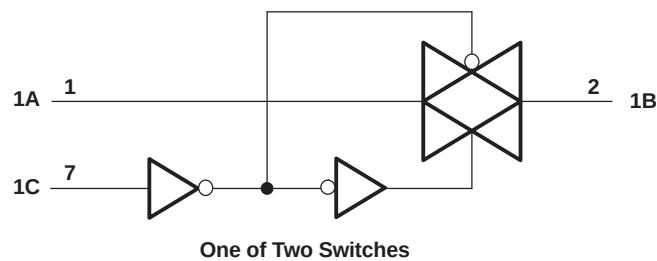
8 Detailed Description

8.1 Overview

This dual bilateral analog switch is designed for 1.65-V to 5.5-V V_{CC} operation. Robust LVC family technology allows this device to accept input voltages without connecting power to V_{CC} .

The SN74LVC2G66 device permits signals with amplitudes of up to 5.5 V (peak) to be transmitted in either direction. A high-level voltage applied to the control pin C enables the respective switch to begin propagating signals across the device. A low-level voltage disables this transmission. Each device incorporates two switches with independent control and operation.

8.2 Functional Block Diagram



8.3 Feature Description

Each switch section has its own enable-input control (C). A high-level voltage applied to C turns on the associated switch section. When C is this Signals can pass through A to B or B to A. Low ON-resistance of 6 Ω at 4.5-V V_{CC} is ideal for analog signal conditioning systems. The control signals can accept voltages up to 5.5 V without V_{CC} connected in the system. Combination of lower t_{pd} of 0.8 ns at 3.3 V and low enable and disable time make this part suitable for high-speed signal switching applications.

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74LVC2G66.

Table 1. Function Table

CONTROL INPUT (C)	SWITCH
L	Off
H	On

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC2G66 can be used in any situation where an Dual SPST switch would be used and a solid-state, voltage controlled version is preferred.

9.2 Typical Application

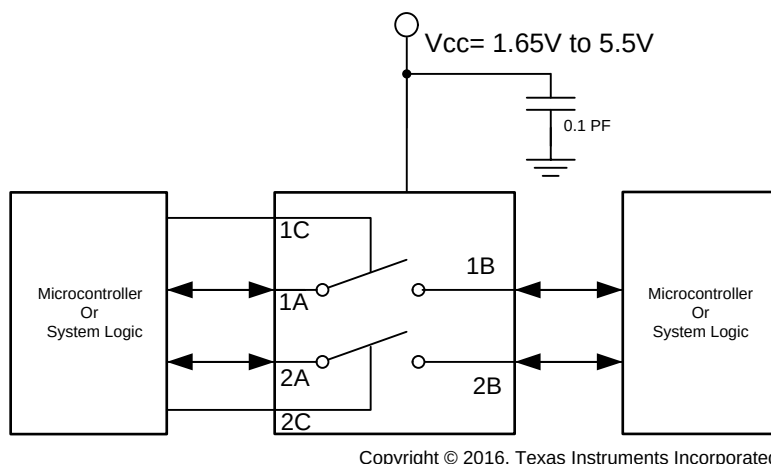


Figure 11. Typical Application Schematic

9.2.1 Design Requirements

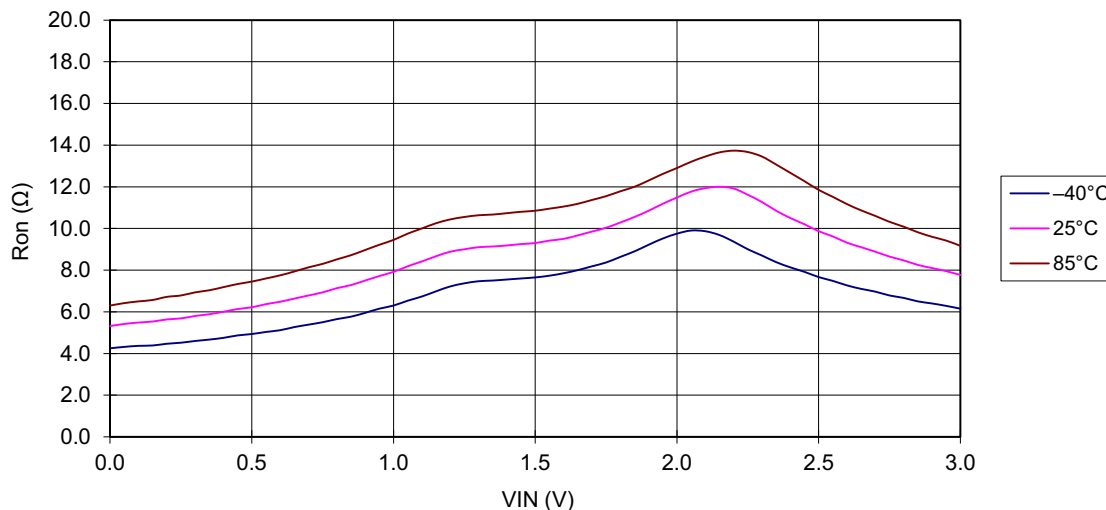
The SN74LVC2G66 allows on/off control of analog and digital signals with a digital control signal. All input signals should remain between 0 V and V_{CC} for optimal operation.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions:
 - For rise time and fall time specifications, see $\Delta t/\Delta v$ in the [Recommended Operating Conditions](#) table.
 - For specified high and low levels, see V_{IH} and V_{IL} in the [Recommended Operating Conditions](#) table.
 - Inputs and outputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC} .
2. Recommended Output Conditions:
 - Load currents should not exceed ± 50 mA.
3. Frequency Selection Criterion:
 - Maximum frequency tested is 150 MHz.
 - Added trace resistance or capacitance can reduce maximum frequency capability; use layout practices as directed in [Layout](#).

Typical Application (continued)

9.2.3 Application Curve



Pin: A–B, $V_{CC} = 3\text{ V}$, $I_S = 24\text{ mA}$

Figure 12. r_{on} vs V_I

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the [Recommended Operating Conditions](#).

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μF bypass capacitor is recommended. If there are multiple pins labeled V_{CC} , then a 0.01- μF or 0.022- μF capacitor is recommended for each V_{CC} because the VCC pins will be tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μF bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μF and 1- μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to loop antenna theory, but different enough to warrant their own discussion. When a PCB trace turns a corner at a 90° angle, a reflection can occur. This is primarily due to the change of width of the trace. At the apex of the turn, the trace width is increased to 1.414 times its width. This upsets the transmission line characteristics, especially the distributed capacitance and self-inductance of the trace — resulting in the reflection.

NOTE

Not all PCB traces can be straight, and so they will have to turn corners. [Figure 13](#) shows progressively better techniques of rounding corners. Only the last example maintains constant trace width and minimizes reflections.

11.2 Layout Example

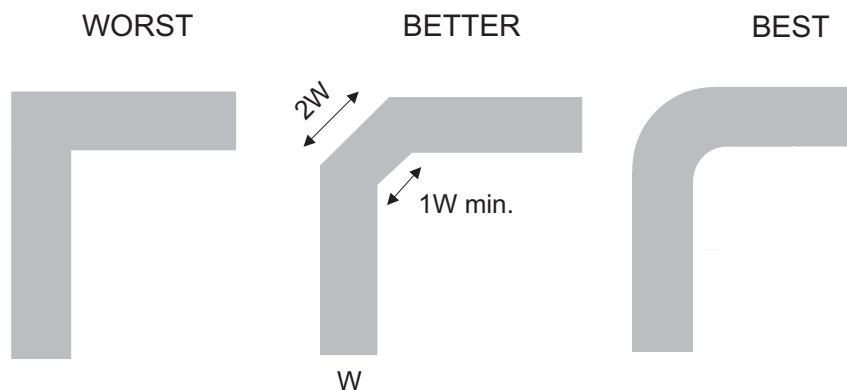


Figure 13. Trace Example

12 器件和文档支持

12.1 社区资源

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12.4 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、缩写和定义。

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74LVC2G66DCTR	Active	Production	SSOP (DCT) 8	3000 LARGE T&R	Yes	NIPDAU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)
SN74LVC2G66DCTR.A	Active	Production	SSOP (DCT) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)
SN74LVC2G66DCTR.B	Active	Production	SSOP (DCT) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)
SN74LVC2G66DCUR	Active	Production	VSSOP (DCU) 8	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(66, C66Q, C66R) CZ
SN74LVC2G66DCUR.A	Active	Production	VSSOP (DCU) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	(66, C66Q, C66R) CZ
SN74LVC2G66DCUR.B	Active	Production	VSSOP (DCU) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	(66, C66Q, C66R) CZ
SN74LVC2G66DCURG4	Active	Production	VSSOP (DCU) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66DCURG4.B	Active	Production	VSSOP (DCU) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66DCUT	Obsolete	Production	VSSOP (DCU) 8	-	-	Call TI	Call TI	-40 to 85	(C66Q, C66R)
SN74LVC2G66DCUTE4	Active	Production	VSSOP (DCU) 8	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66DCUTG4	Active	Production	VSSOP (DCU) 8	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66DCUTG4.B	Active	Production	VSSOP (DCU) 8	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66YZPR	Active	Production	DSBGA (YZP) 8	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(C67, C6N)
SN74LVC2G66YZPR.B	Active	Production	DSBGA (YZP) 8	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(C67, C6N)

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF SN74LVC2G66 :

- Automotive : [SN74LVC2G66-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

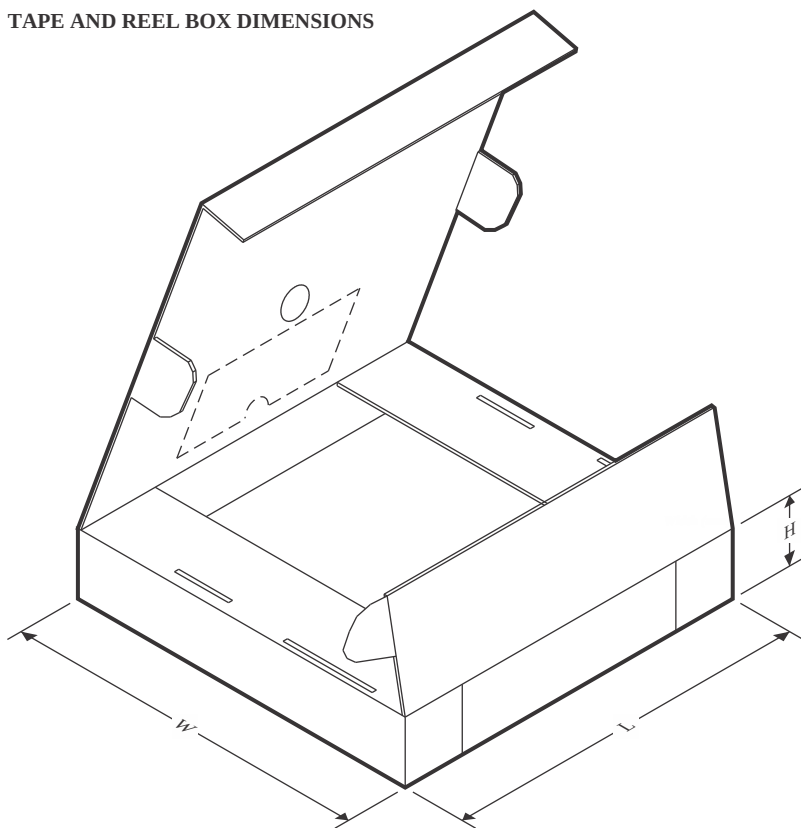
TAPE AND REEL INFORMATION



*All dimensions are nominal

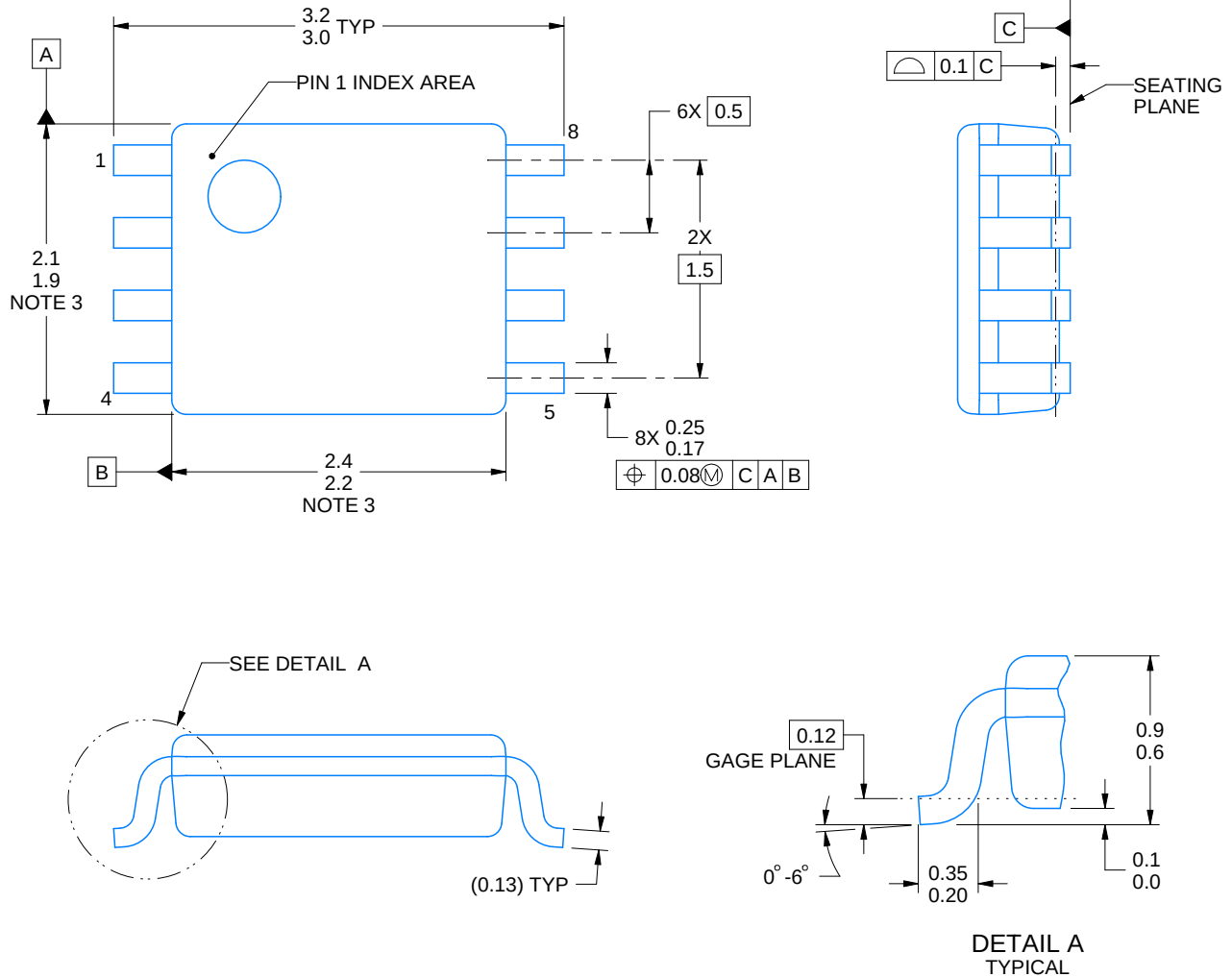
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G66DCTR	SSOP	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G66DCTR	SSOP	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2G66DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G66DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G66YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0



4225266/A 09/2014

NOTES:

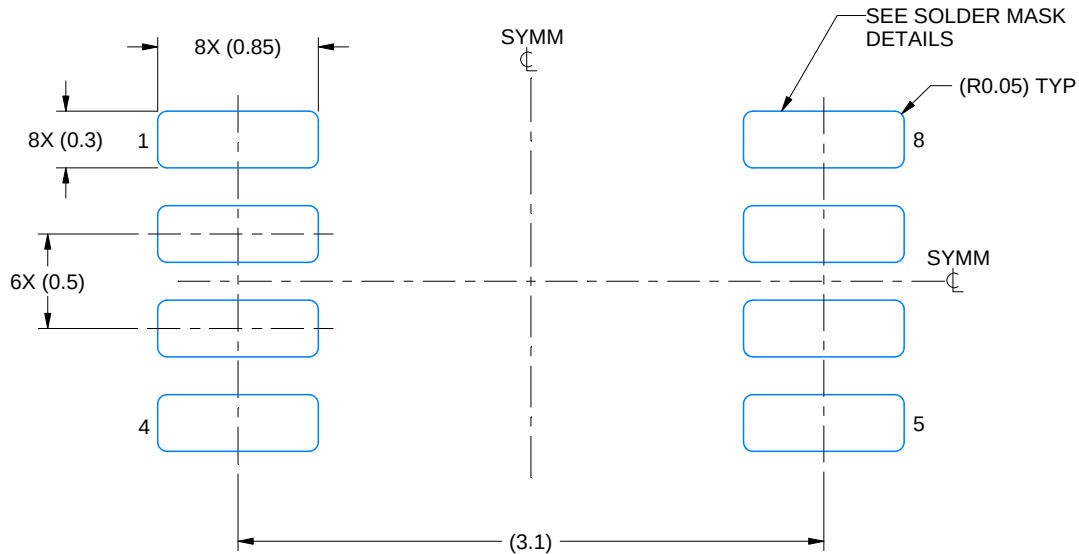
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-187 variation CA.

EXAMPLE BOARD LAYOUT

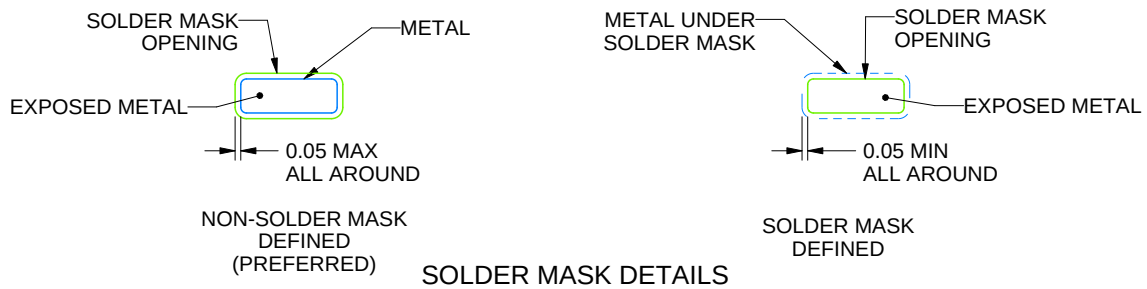
DCU0008A

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 25X



4225266/A 09/2014

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

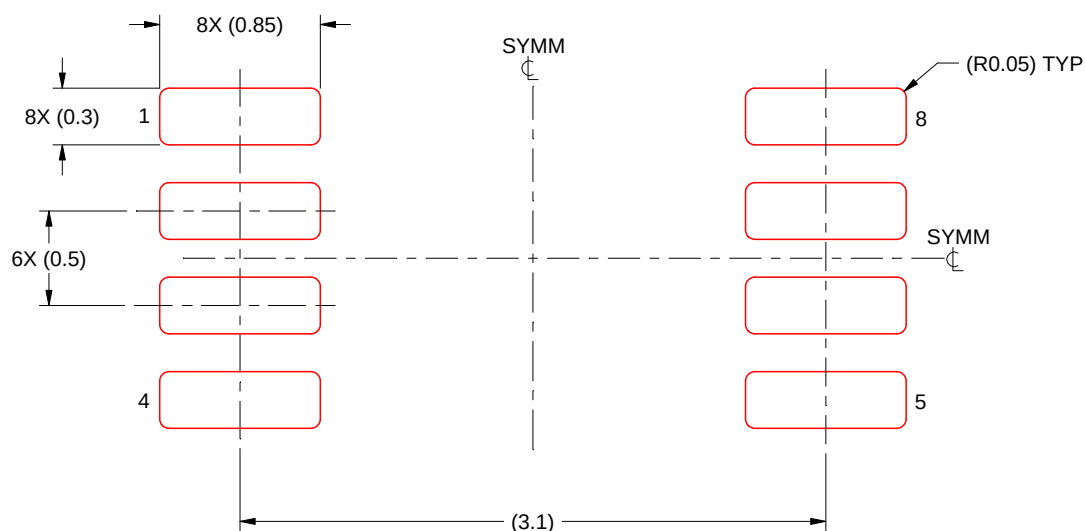
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCU0008A

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 25X

4225266/A 09/2014

NOTES: (continued)

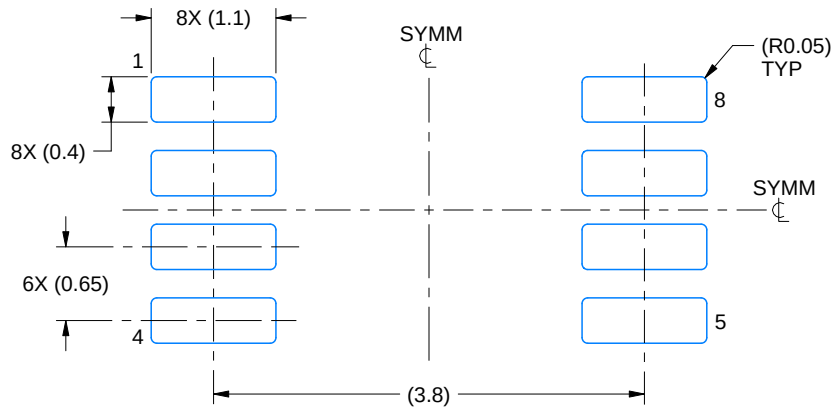
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

EXAMPLE BOARD LAYOUT

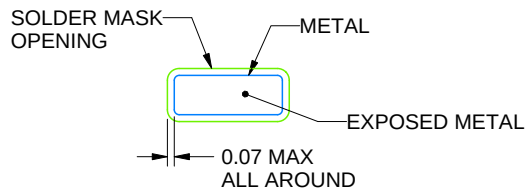
DCT0008A

SSOP - 1.3 mm max height

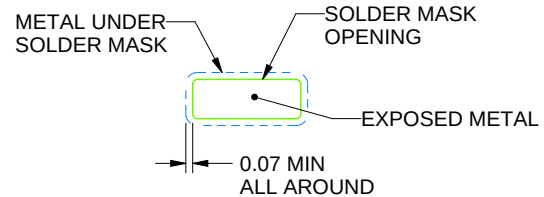
SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



NON SOLDER MASK
DEFINED



SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4220784/C 06/2021

NOTES: (continued)

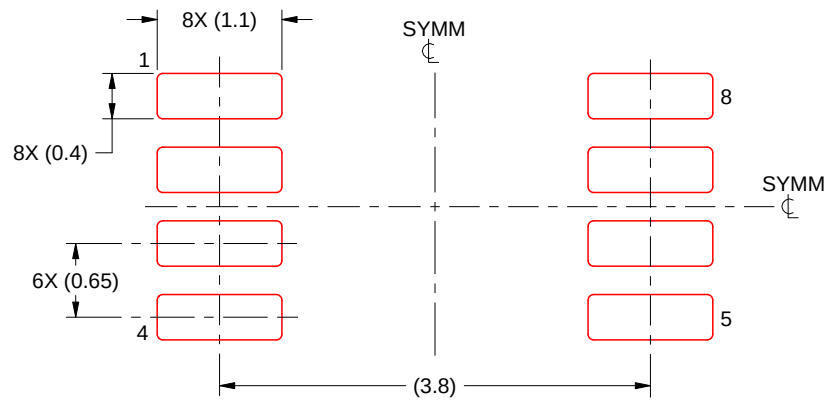
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCT0008A

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



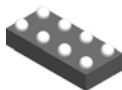
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4220784/C 06/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

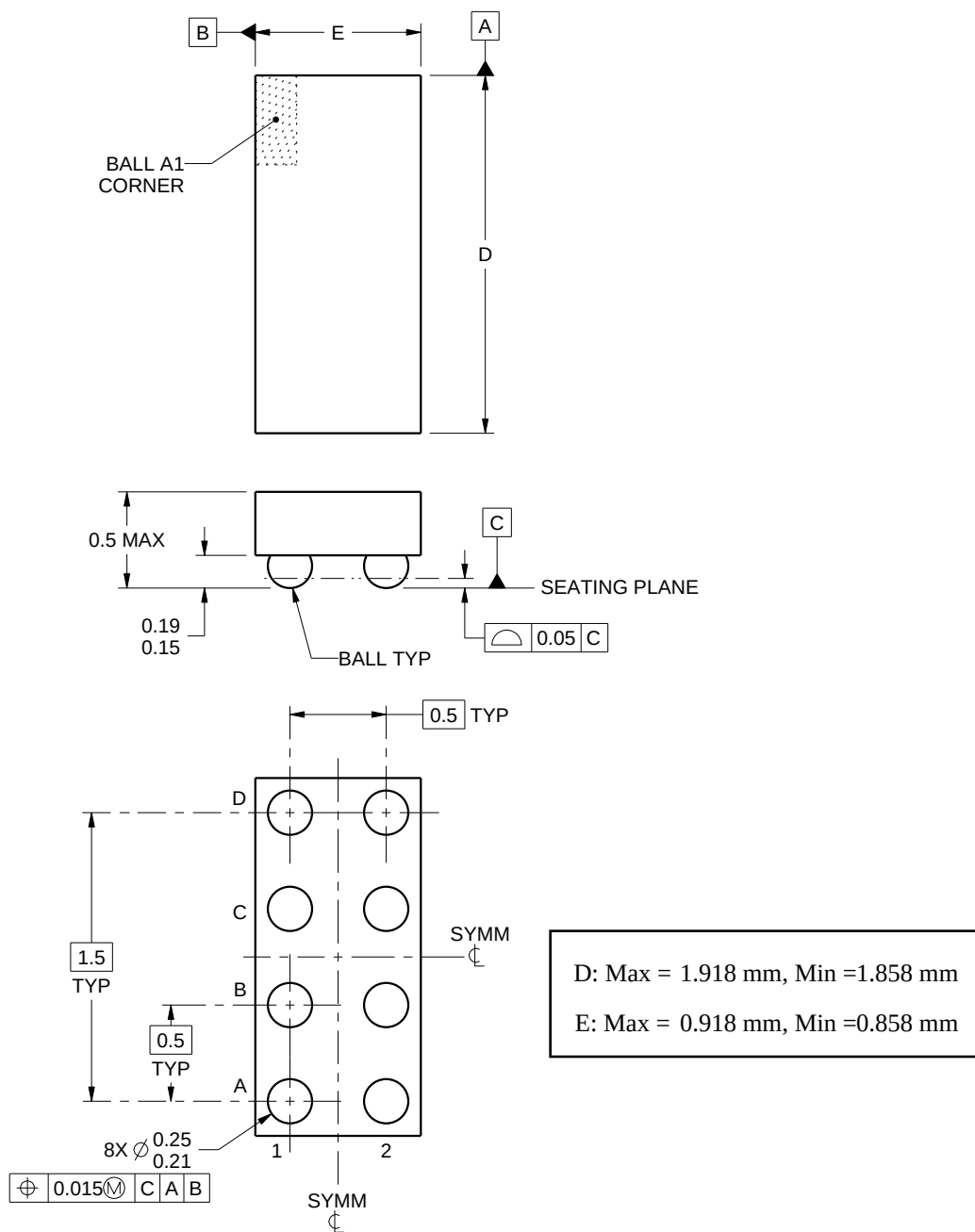
YZP0008



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



4223082/A 07/2016

NOTES:

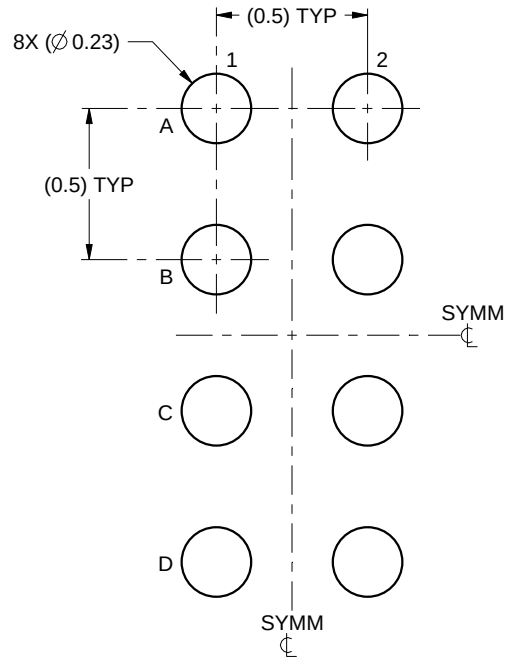
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

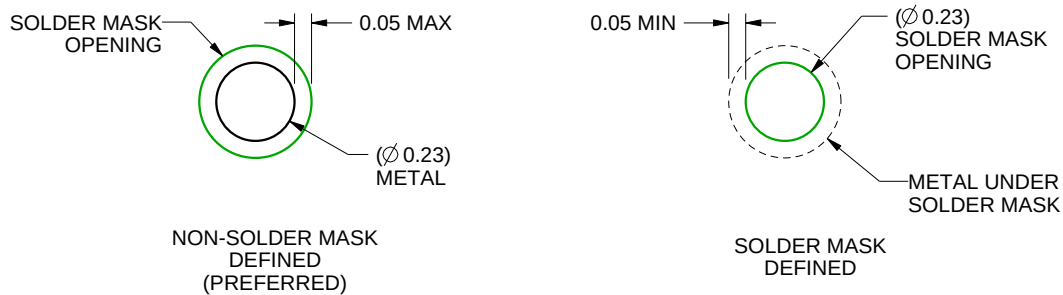
YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
SCALE:40X

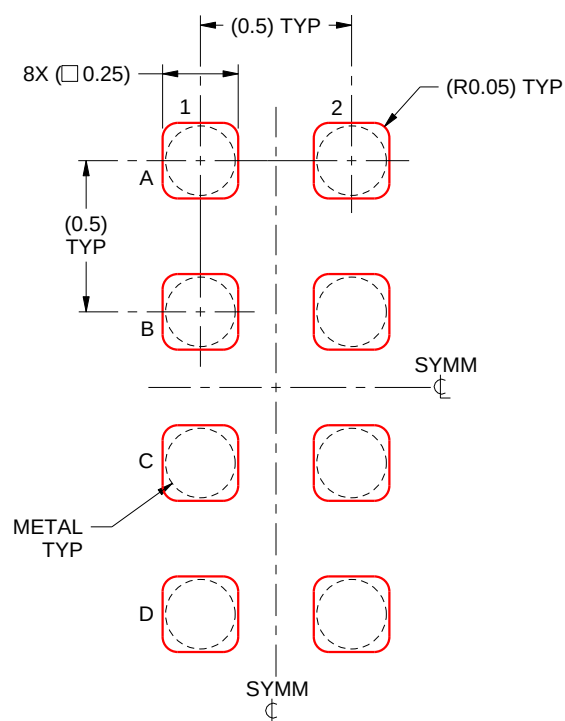


SOLDER MASK DETAILS
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

- Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



SOLDER PASTE EXAMPLE
 BASED ON 0.1 mm THICK STENCIL
 SCALE:40X

4223082/A 07/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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